The reactions of gallium metal with $(p-MeOC_6H_4)_3AsI_2$ and Et_3AsI_2 ; isolation of a novel gallium(II) arsine complex with a gallium–gallium bond and the X-ray crystal structures of $GaI_3[(p-MeOC_6H_4)_3As]$ and $Ga_2I_4(AsEt_3)_2$

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The reactions of $(p-\text{MeOC}_6H_4)_3\text{AsI}_2$ and Et_3AsI_2 with gallium metal powder produce the metal complexes $\text{GaI}_3[(p-\text{MeOC}_6H_4)_3\text{As}]$ and $\text{Ga}_2\text{I}_4(\text{AsEt}_3)_2$, respectively; the latter represents a unique example of a gallium-tertiary arsine complex containing a gallium-gallium bond, and both structures illustrate the subtle effect of the organic substituent on the arsenic atoms.

In contrast to the transition metals,¹ the chemistry of the main group metals containing tertiary phosphine and arsine donor ligands has received little attention; and there is little data concerning the structural nature of gallium complexes containing tertiary phosphine and arsine donor ligands. This has been illustrated in a recent review of this area by Norman,² who points out that workers have investigated a small number of triorganogallium phosphine complexes, R₃Ga(PR₃), e.g. GaMe₃(PMe),³ Ga(CH₂Bu^t)₃(PHPh₂)⁴ and GaPh₃[P(SiMe₃)₃].⁵ In all cases, these complexes have distorted tetrahedral or trigonal-based pyramidal geometry for the gallium centre, dependent on the steric bulk of the ligands concerned. The diphosphine complex GaMe₃(Ph₂PCH₂CH₂PPh₂) has also been structurally characterised,⁶ showing the gallium centre in tetrahedral geometry. Only one gallium trihalide complex containing a tertiary phosphine bond has been structurally characterised, GaCl₃(PMe₃),⁷ which again contains the gallium in tetrahedral geometry. No gallium halide complexes containing a tertiary arsine donor ligand were known until very recently: GaI₃(AsPh₃)⁸ has been synthesised from the reaction of GaI₃·OEt₃ with AsPh₃; this molecular tetrahedral complex was found to be in equilibrium with the ionic complex [Ph₃AsI][GaI₄], and the latter represents the first arsenic(v) iodo complex to be crystallographically characterised.

There has also been great interest recently in certain gallium complexes for potential applications as MOCVD precursors *e.g.* [ButGaS]₄,^{9,10} [(Et₂MeC)GaS]₄ and [ButGaSe]₄;¹¹ clearly, although a largely unexplored field, it may be expected that interest will grow rapidly.

We are engaged in a study of the oxidising power of a variety of R_3EX_2 compounds (E = P, As, Sb; $X_2 = Br_2$, I_2 , IBr) with unactivated metal powders in diethyl ether solution.¹²⁻¹⁷

We have now turned our attention to the reaction of these new oxidising agents with gallium metal powder, principally for two reasons: first, very little is known concerning the coordination chemistry of gallium(III) halides with tertiary arsine donor ligands, and, secondly, such complexes may have applications in the microelectronics industry as precursors for MOCVD. (p-MeOC₆H₄)₃AsI₂ reacts with gallium metal powder according to eqn. (1).

$$3(p-\text{MeOC}_{6}\text{H}_{4})_{3}\text{AsI}_{2} + 2\text{Ga} \xrightarrow[\text{Et}_{2}\text{O}]{} \underbrace{\xrightarrow{ca. \text{ ld, Ar}}_{\text{Et}_{2}\text{O}}}_{2\text{GaI}_{3}[(p-\text{MeOC}_{6}\text{H}_{4})_{3}\text{As}]}$$
(1)

Recrystallisation of the white powder from diethyl ether solution produced a large quantity of colourless crystals,[†] from which one was selected for analysis by single-crystal X-ray diffraction. The structure[‡] of the gallium complex was revealed to be $GaI_3[(p-MeOC_6H_4)_3As]$, Fig. 1. The gallium atom is in the expected tetrahedral environment; however, this stoichiometry has only one precedent, GaI₃(AsPh₃), synthesised by Baker et al. from the direct reaction of gallium triiodide and a triphenylarsine.⁸ The synthesis of GaI₃[(p-MeOC₆H₄)₃As] described here indicates that gallium(III) tertiary arsine complexes are also available from our new synthetic route, viz. the direct reaction of gallium metal with R₃AsI₂ species. In contrast to the findings of Baker et al.,8 no equilibrium with the arsenic(v) complex [(p-MeOC₆H₄)₃AsI][GaI₄] was observed. This may be due to the greater basicity of $(p-MeOC_6H_4)_3As$ compared to Ph₃As, thus rendering the gallium-arsenic bond stronger in the complex described here and therefore less susceptible to cleavage by diiodine.

 Et_3AsI_2 reacts with gallium metal powder according to eqn. (2).

$$2Et_3AsI_2 + 2Ga \rightarrow [GaI_2(AsEt_3)_2]_2$$
(2)



Fig. 1 Perspective view of the molecular structure of $GaI_3[(p-MeO-C_6H_4)_3As]$. Selected bond lengths (Å) and angles (°): Ga-I(1) 2.505(1), Ga-As 2.509(3), Ga-As-C(1) 114.0(3), I(1)-Ga-I(1) 111.62(5), I(1)-Ga-As 107.23(5).

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Fig. 2 Perspective view of the molecular structure of $[GaI_2(AsEt_3)]_2$. Selected bond lengths (Å) and angles (°): Ga–Ga 2.428(7), Ga–I(1) 2.564(4), Ga–I(2) 2.568(4), Ga–As 2.484(5); I(1)–Ga–I(2) 109.0(1), I(1)–Ga–As 101.8(2), I(1)–Ga–Ga' 115.7(2), I(2)–Ga–As 101.6(2), I(2)–Ga–Ga' 113.0(2), As–Ga–Ga' 114.4(2).

Recrystallisation of the white powder[†] from diethyl ether solution at 0 °C produced a large quantity of colourless crystals, from which one was selected for analysis by single-crystal Xray diffraction, revealing the dinuclear gallium(II) complex [GaI₂(AsEt₃)₂]₂.‡ This is a very surprising result, since we had anticipated a monomeric tetrahedral gallium(III) complex analogous to the tertiary arsine complex described above, and in agreement with the findings of Baker et al.⁸ The gallium atoms are in tetrahedral geometry linked by a Ga-Ga bond of 2.428(7) Å. The gallium–arsenic bond is 2.484(5) Å, similar to that found for GaI₃(AsPh₃), 2.490(5) Å. Although no complexes are known of a gallium-gallium bonded species containing tertiary arsine donor ligands, there nevertheless exist some crystallographically characterised gallium(II) com- plexes containing a gallium-gallium bond. The complexes of general formula $Ga_2X_4L_2$ (X = Cl,¹⁹, Br,²⁰ L = dioxane; X = Br, L = pyridine)²¹ have been crystallographically characterised by Small and coworkers. The gallium-gallium bond lengths for these three complexes were found to be 2.406(1), 2.395(6) and 2.421(3) Å, respectively, similar to $Ga_2I_4(AsEt_3)_2$, 2.428(7) Å, described here. Additionally, the organometallic complex $[Li([12]crown-4)_2]^+[Ga_2(C_6H_3Pr_{3}^{i}-2,4,6)]^{22}$ has recently been synthesised and shown to have Ga-Ga multiple bonding character, this phenomenon being reflected in the shorter gallium-gallium bond distance, 2.343(2) Å. Finally the interesting cluster compound $[{(Et_2O)_2ClGa}Ga{GaCl_2(Et_2O)}_3]^{23}$ containing a tetrahedral Ga₅ unit is known, which exhibits gallium-gallium bonds ranging from 2.417(2) to 2.450(2) Å. Again, in contrast to the findings of Baker et al.8 no evidence for the formation of an arsenic(v) species, [R₃AsI][GaI₄], was noted even on standing for several weeks.

Footnotes

[†] GaI₃[(*p*-MeOC₆H₄)₃As], colourless crystals, *ca.* 70% yield, mp 160–161 °C, correct elemental analysis (C, H, I). ¹H NMR spectrum: δ 3.7 (s), 6.9 (d), 7.3 (d); relative intensities (3:2:2). Low-frequency Raman spectrum (50–550 cm⁻¹): 74 (Ga–As), 143 cm⁻¹ (Ga–I).

 $[GaI_2(AsEt_3)_2], \ quantitative \ yield, \ colourless \ crystals, \ mp \ 134-135 \ ^oC, \ correct \ elemental \ analysis \ (C, H, I). \ ^H \ NMR \ spectrum: \ \delta \ 1.2 \ (s), \ 1.4 \ (m), \ (m),$

2.1 (m); relative intensities (3:2:2). Low-frequency Raman spectrum $(50-550 \text{ cm}^{-1})$: 72 (Ga-As), 142 (Ga-I), 222 cm⁻¹ (Ga-Ga).

 $\ddagger Crystal data:$ for GaI₃[As(p-MeOC₆H₄)₃]: trigonal, space group $P\overline{3}$ (no. 147), a = 13.130(5), c = 8.846(4) Å, U = 1321(2) Å³, $Z = 2, D_c = 2.129$ $g \text{ cm}^{-3}, \mu = 57.68 \text{ cm}^{-1}, F(000) = 788$. The structure analysis is based on 5224 reflections (Mo-K α , $\theta_{max} = 50.10^{\circ}$), 967 observed [($I > 3.00\sigma(I)$], 88 parameters. Absorption correction (min., max. transmission 0.74, 1.15). The structure was solved by direct methods and refined by full-matrix least squares. Final residuals R = 0.049, $R_w = 0.050$. For $[GaI_2(AsEt_3)]_2$: monoclinic, space group, $P2_1/n$ (no. 14), a = 10.137(4), b = 12.225(5), c = 10.895(5) Å, $\beta = 92.34(3)^\circ$, U = 1349(2) Å³, Z = 2, $D_c = 2.391$ $g \text{ cm}^{-3}, \mu = 89.48 \text{ cm}^{-1}, F(000) = 884$. The structure analysis is based on 2432 reflections (Mo-K α , 2 $\theta_{max} = 50.1^{\circ}$), 539 observed [$I > 3.00\sigma(I)$], 92 parameters. Absorption correction (min., max. transmission 0.80, 1.07). The structure was solved by direct methods and refind by full-matrix least squares. Final residuals R = 0.040, $R_w = 0.038$. Atomic coordinates, bond lengths and angles, and thermal parameters have been deposited at the Cambridge Crystallographic Data Centre (CCDC). See Information for Authors, Issue No. 1. Any request to the CCDC for this material should quote the full literature citation and the reference number 182/114.

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